

LISTING OF CLAIMS:

1. (Previously Presented) A process for depositing a silver film on a substrate, comprising depositing silver on the substrate by chemical vapor deposition, in an oxygen atmosphere or in a hydrogen atmosphere, of a solution comprising a silver precursor, an amine and/or a nitrile, and a solvent, wherein:
 - the silver precursor is a silver carboxylate RCO_2Ag in which R is a linear or branched alkyl radical that has 3 to 7 carbon atoms;
 - the concentration of the silver precursor in the solution is between 0.01 and 0.6 mol/l;
 - optionally the solvent has an evaporation temperature that is less than the decomposition temperature of the silver precursor; and
 - the percentage by volume of the amine and/or the nitrile in the solvent is more than 0.1%.
2. (Previously presented) The process according to claim 1, wherein the silver precursor is the silver pivalate $(\text{CH}_3)_3\text{-C-CO}_2\text{Ag}$.
3. (Previously presented) The process according to claim 1, wherein the solvent is an organic compound that is liquid at ambient temperature and up to about 200°C under normal pressure conditions.
4. (Previously presented) The process according to claim 3, wherein the solvent is selected from the group consisting of mesitylene, cyclohexane, xylene, toluene and n-octane.
5. (Previously presented) The process according to claim 1, wherein the amine is a monoamine that is selected from the group consisting of n-hexylamine, isobutylamine, disec-butylamine, triethylamine, benzylamine, ethanolamine and diisopropylamine.
6. (Previously presented) The process according to claim 1, wherein the amine is a polyamine.

7. (Previously presented) The process according to claim 1, wherein the nitrile is selected from the group consisting of acetonitrile, valeronitrile, benzonitrile and propionitrile.

8. (Previously presented) The process according to claim 1, wherein the substrate is formed by a material that is selected from the group consisting of superconductive high T_c materials, ceramics, thermoresistant polymers, glasses, MgO, LaAlO₃, Ni, Si, AsGa, InP, SiC and SiGe.

9. (Previously presented) The process according to claim 1, wherein the temperature of the substrate on which silver is to be deposited is between 200 and 450°C.

10. (Cancelled)

11. (Previously presented) The process according to claim 1, wherein silver is deposited on the substrate in the presence of a cold plasma.